# A selfconsistent theory of current-induced sw itch ing of $m$ agnetization 

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A selfconsistent theory of the current-induced sw itching of $m$ agnetization using nonequilibrium K eldysh form alism is developed for a junction of two ferrom agnets separated by a nonm agnetic spacer in the ballistic lim it. It is shown that the spin-transfer torques responsible for currentinduced sw itching of $m$ agnetization can be calculated from rst principles in a steady state when the $m$ agnetization of the sw itching $m$ agnet is stationary. A steady state is achieved when the spintransfer torque, proportional to bias voltage in the linear response regim $e$, is balanced by the torque due to anisotropy elds. The spin-transfer torque is expressed in term s of one-electron surface $G$ reen functions for the junction cut into tw o independent parts by a cleavage plane im $m$ ediately to the left and right of the sw itching $m$ agnet. T he surface $G$ reen functions are calculated using a tight-binding H am iltonian w ith param eters determ ined from $\mathrm{a} t$ to an ab in itio band structure. This treatm ent yields the spin transfer torques taking into account rigorously contributions from all the parts of the junction. The spin-transfer torque has two components, one $w$ ith the torque vector $T_{k}$ in the plane containing the $m$ agnetizations of the tw o $m$ agnetic layers and another $w$ th the torque vector $T_{\text {? }}$ perpendicular to this plane. It is show $n$ that, in general, $T_{k}$ and $T_{\text {? }} m$ ay be comparable in $m$ agnitude and they both tend to nite values independent of the spacer thickness in the lim it of a thick spacer. $T$ ? is show $n$ to be sm allw hen the exchange splitting of the $m$ a jority-and $m$ inority-spin bands in both ferrom agnets tends to in nity or in the case when the junction has a plane of re ection sym $m$ etry at the center of the spacer. $T$ he torques $T_{\text {? }}$ and $T_{k}$ are com parable for a $C o / C u / C o$ (111) junction when the switching $C o$ layer is one or two atom ic planes thick. $T_{?}$ is $27 \%$ of $T_{k}$ even for a sw itching $C \circ m$ agnet of ten atom ic planes. $D$ epending on $m$ aterial param eters of the junction, the relative sign of $\mathrm{T}_{\text {? }}$ and $\mathrm{T}_{\mathrm{k}}$ can be negative as well as positive. In particular, $\mathrm{T}_{\text {? }}=\mathrm{T}_{\mathrm{k}}<0$ for $\mathrm{Co} / \mathrm{Cu} / \mathrm{Co(111)}$ w ith sw itching Com agnet of one atom ic plane and $\mathrm{T}_{\text {? }}=\mathrm{T}_{\mathrm{k}}>0$ for two atom ic planes of Co. A negative sign of the ratio $T_{?}=T_{k}$ has a profound e ect on the nature of sw itching, particularly in the realistic case of easy-plane (shape) anisotropy m uch larger than in-plane uniaxial an isotropy. To calculate the hysteresis loops of resistance versus current, and hence to determ ine the critical current for sw itching, the $m$ icroscopically calculated spin-transfer torques are used as an input into the phenom enological Landau-L ifshitz equation with $G$ ilbert dam ping. In the absence of an applied $m$ agnetic eld, an ordinary hysteresis loop is the only possible sw itching scenario when $\mathrm{T}_{?}=\mathrm{T}_{\mathrm{k}}>0$. H ow ever, for $\mathrm{T}_{?}=\mathrm{T}_{\mathrm{k}}<0$, a norm al hysteretic sw itching occurs only at relatively low current densities. W hen the current exceeds a critical value, there are no stable steady states and the system thus rem ains perm anently in a tim e dependent state. T his is analogous to the observed precession of the switching $m$ agnet $m$ agnetization caused by a DC current in the presence of an applied $m$ agnetic eld. The present calculations for $\mathrm{Co} / \mathrm{Cu} / \mathrm{Co(111)}$ show that the critical current for sw itching in the hysteretic regim e is $10^{7} \mathrm{~A}=\mathrm{cm}^{2}$, which is in good agreem ent w ith experim ent.

## IN TRODUCTION

Slonczew ski [112] proposed a new $m$ ethod of sw itching the $m$ agnetization direction of a thin $m$ by $m$ eans of a spin-polarized current. T he current is spin-polarized by passing through a thick layer of a ferrom agnetic $m$ etal, whose $m$ agnetization is assum ed to be pinned, subsequently passing through a nonm agnetic $m$ etallic spacer layer and then through a thin $m$ agnetic $s w$ itching layer into a nonm agnetic lead. Early related theoreticalw ork is due to Berger [1]. Sw itching of the m agnetization is accom panied by a change in resistance (CPP GMR) and thee ect hasbeen observed experim entally by studying hysteresis loops in resistance versus current plots for pillar system s [3, current and static $m$ agnetization, just as in the Stonerw ohlfarth $\left[\begin{array}{l}-1\end{array}\right]$ theory of eld-sw itching jum ps occur betw een equilibrium states. W e have form ulated a rst-principle theory of current-induced sw itching based on this idea. A s in the Stoner-W ohlfarth theory, we assum e that the sw itching $m$ agnet rem ains single dom ain during the sw itching process.

O ne of the m ain aim s of this paper is to calculate hysteresis loops of resistance versus current from rst principles for a much $m$ ore general situation than has been considered previously. In previous treatm ents a uniaxial anisotropy eld was introduced in the switching $m$ agnet $w$ ith its direction parallel to the $m$ agnetization of the polarizing $m$ agnet []$\left._{[1}\right],\left[\underline{I n}_{1}^{1}\right]$. In this case, there are only two steady states in which the $m$ agnetizations of the polarizing and sw itching $m$ agnets are either parallel or antiparallel. It is for this reason that the steady-state approach has not previously been further developed. H ow ever, in real experim ents on pillar structures shape anisotropy due to variable shape of pillar cross sectionsm eans that the direction of the anisotropy eld in the sw itching $m$ agnet is not sim ply related to the direction of the $m$ agnetization of the polarizing $m$ agnet. Furtherm ore, in som e experim ents $[\underline{G}],\left[\begin{array}{l}1 \\ 1\end{array}\right]$ an extemal eld is also applied so that $m$ ore general orientations of the $m$ agnetizations occur in the steady states. It is, therefore, essential to consider a com pletely general case when the uniaxial anisotropy eld $m$ akes an arbitrary angle $w$ ith the polarizing m agnetization. W e also include the easy plane anisotropy, which is alw ays large in layered magnets, and investigate fully its consequences.

In a steady state there is a balance betw een the spin-current torque, acting on the sw itching $m$ agnet due to the spin-polarized current, and the torque due to anisotropy and extemal elds. In our general rst-principle treatm ent, two com ponents of the spin-current torque appear naturally, one $w$ th the torque vector $T_{k}$ in the plane containing the $m$ agnetizations of the tw o $m$ agnetic layers ('in-plane' torque) and another w ith the torque vector $\mathrm{T}_{\text {? }}$ perpendicular to this plane ('out-of-plane' torque). Slonczew ski [1] considered only $\mathrm{T}_{\mathrm{k}} \mathrm{l}$ and it is generally believed $\left[\bar{q}_{1}^{1}\right]$ that $T$ ? is negligible. $W$ e start the presentation of our results in Sec. 6 by deriving
 appears. It $w$ ill be seen that this result is not alw ays valid but is just an artefact of $\overline{\text { S lonczew ski's sim ple }}$ m odel. In fact, we shall show that in som e cases $\mathrm{T}_{\text {? }}$ is dom inant and that, even when sm all, $\mathrm{T}_{\text {? }}$ is essential since its im portance is strongly enhanced in the presence of easy-plane anisotropy.

To calculate hysteresis loops for this general scenario, w e need to solve the follow ing problem s: (i) calculate $m$ icroscopically both the in-plane and out-of-plane com ponents of the spin-current torque; (ii) determ ine the steady states which form the continuous parts of the hysteresis curve; (iii) investigate the stability of such states in order to determ ine critical currents at which the jum ps, and hence sw itching, occur; (iv) calculate the resistance of the layered structure along the steady-state paths.

W ithin our uni ed theory, all this can be done for a general layered system $w$ th a fully realistic band structure.
A jump in the hysteresis curve occurs at a critical current when one steady state becom es unstable and the system seeks out another stable steady state. $T$ his is in analogy with the Stoner-w ohlfarth [ALT] theory of
eld-sw itching where one deals w ith equilibrium states instead of the present nonequilibrium steady states. As in that theory we do not concem ourselves with the detailed dynam ics of the sw itching. H ow ever, we identify in this paper certain cases in which one steady state becom es unstable above a critical current but there are no other stable steady states available. U nder these circum stances the $m$ agnetization of the sw itching layer rem ains perpetually in a tim e-dependent state.

In order to study nonequilibrium steady states we use the K eldysh form alism $\left.[\overline{9}],[1]\left[\begin{array}{c}{[1]}\end{array}\right][]_{1}^{1}\right]$ described in Sec. 3. As pointed out above, the steady state arises from a balance between spin-current torque and anisotropy eld torque. H ence it is essential to include anisotropy and/or extemal elds in the H am iltonian of the system from the outset. It is also necessary to treat correctly the on-site electron-electron interaction $w$ hich is responsible for the spontaneous $m$ agnetization of the polarizing and $s w$ itching $m$ agnets. This is achieved by insisting that the local exchange eld is in the direction of the localmagnetization, which is the essential feature of self-consistent eld approxim ations such as unrestricted $H$ artree $F$ ock ( $\mathrm{H} F$ ) and local spin density (LSDA). Such a treatm ent respects the spin-rotational sym m etry of the ferrom agnet in the absence of extemal elds. Beyond this we do not need to introduce a self-consistent treatm ent of the C oulom b interaction explicitly, although bulk LSD A calculations underlie the band param eters and exchange splittings used in our calculations. In our K eldysh approach the direction ofm agnetization in each atom ic plane of the sw itching $m$ agnet is determ ined self-consistently in the steady state by the requirem ent that the $m$ agnetization of a given atom ic plane is parallel to the exchange eld in that plane. The relationship betw een this approach and the $m$ ore intuitive one ofbalancing torques is discussed in Secs. 2 and 5.
$T$ he treatm ent described above enables us to determ ine all possible steady states of the system and the next step is to investigate their stability. W e do this by introducing the spin-current torques, calculated $m$ icroscopically as functions ofm agnetization direction, and anisotropy torques into a Landau- ifshitz equa-
tion ofm otion for the $m$ agnetization including $G$ ibert dam ping. W e linearize the equation ofm otion about the steady-state solution to obtain the conditions for stability.

Finally, we construct hysteresis curves from continuous steady-state paths and jum ps at points of instability.

THEORETICALMODEL

T he layer structure we consider is shown in Fig.1. It consists of a


F IG . 1: Schem atic picture of a $m$ agnetic layer structure for current-induced sw itching ( $m$ agnetic layers are darker, non-m agnetic layers lighter).
sem i-in nite polarizing ferrom agnet $w$ th $m$ agnetization $P$, a nonm agnetic $m$ etallic spacer $w$ ith $N$ atom ic planes, a sw itching $m$ agnet $w$ ith $M$ atom ic planes, and a sem i-in nite nonm agnetic lead of the sam em aterial as the spacer. E ach layer is described by a tight-binding model, in generalm ultiorbitalw ith $s, p$, and $d$ orbitals whose one-electron param etens are tted to rst-principle bulk band structure, as discussed previously [12]. T he H am iltonian is, therefore, of the form

$$
\begin{equation*}
\mathrm{H}=\mathrm{H}_{0}+\mathrm{H}_{\text {int }}+\mathrm{H}_{\text {an is }} ; \tag{1}
\end{equation*}
$$

where the one-electron hopping term $\mathrm{H}_{0}$ is given by
where $\mathrm{c}_{\mathrm{k}_{\mathrm{k}} \mathrm{m}}^{\mathrm{y}}$ creates an electron in a B loch state, w ith in-plane w ave vector $\mathrm{k}_{\mathrm{k}}$ and spin , form ed from a given atom ic orbital in plane $m$. $H_{\text {int }}$ is an on-site interaction between electrons in d orbitals which leads to an exchange splitting of the bands in the ferrom agnets and is neglected in the spacer and lead. $T$ he $m$ agnetization of the polarizing $m$ agnet is assum ed to be pinned in the $(z, x)-p l a n e, m$ aking an angle w ith the z axis, as show n in F ig.1. H an is contains e ective elds in the sw itching m agnet corresponding to uniaxial $H \mathrm{u}$ and easy-plane $\mathrm{H}_{\mathrm{p}}$ anisotropies. It is given by

$$
\begin{equation*}
\mathrm{H}_{\mathrm{an} \text { is }}=\mathrm{S}_{\mathrm{n}}: \mathrm{H}_{\mathrm{A}} \text {; } \tag{3}
\end{equation*}
$$

where $S_{n}$ is the operator for the total spin angularm om entum of plane $n$ and

$$
\begin{equation*}
H_{A}=H_{u}+H_{p}: \tag{4}
\end{equation*}
$$

$H_{u}$ and $H p$ are given by

$$
\begin{gather*}
H_{u}=\left(e_{z}:<\overline{S_{n}}>\right) H_{u 0} e_{z}  \tag{5}\\
H_{p}=\left(e_{\mathrm{y}}:<\overline{S_{\mathrm{n}}}>\right) H_{p 0} e_{y} ; \tag{6}
\end{gather*}
$$

$w$ here $<\overline{S_{n}}>$ is a unit vector in the direction of the therm al average of $S_{n}$, and $e_{x}, e_{y}, e_{z}$ are unit vectors in the direction of the axes show $n$ in $F$ ig.1. $\mathrm{H}_{\mathrm{u} 0}, \mathrm{H}_{\mathrm{p}} \mathrm{m}$ easure the strengths of the uniaxial and easy-plane anisotropies and have dim ensions of frequency. These quantities $m$ ay be converted to a eld in tesla by $m$ ultiplying them by $\sim=2 \quad$ в $=5: 69 \quad 10^{12}$. W e assum e that anisotropy elds are uniform throughout the sw itching $m$ agnet but it would be easy to generalize to include, for exam ple, a surface anisotropy. The spin angular $m$ om entum operator $S_{n}$ is given by

$$
\begin{equation*}
\mathrm{S}_{\mathrm{n}}=\frac{1}{2} \sim_{\mathrm{k}_{\mathrm{k}}}^{\mathrm{X}}\left(\mathrm{c}_{\mathrm{k}_{\mathrm{k}} \mathrm{n}}^{\mathrm{y}} ; \mathrm{C}_{\mathrm{k}_{\mathrm{k}} \mathrm{n} \#}^{\mathrm{y}}\right) \quad\left(\mathrm{c}_{\mathrm{k}_{\mathrm{k}} \mathrm{n}} ; ; \mathrm{c}_{\mathrm{k}_{\mathrm{k}} \mathrm{n}} \#\right)^{\mathrm{T}} \tag{7}
\end{equation*}
$$

and the corresponding operator for spin angular $m$ om entum current between planes $n \quad 1$ and $n$ is

$$
\begin{equation*}
j_{\mathrm{n} 1}=\frac{1}{2}_{\mathrm{k}_{\mathrm{k}}}^{\mathrm{X}} \mathrm{~T}\left(\mathrm{k}_{\mathrm{k}}\right)_{\mathrm{n}} ; \mathrm{n} 1 \quad\left(\mathrm{C}_{\mathrm{k}_{\mathrm{k}} \mathrm{n}}^{\mathrm{y}} ; \mathrm{C}_{\mathrm{k}_{\mathrm{k}} \mathrm{n} \#}^{\mathrm{y}}\right) \quad\left(\mathrm{C}_{\mathrm{k}_{\mathrm{k}} \mathrm{n} 1} \| ; \mathrm{C}_{\mathrm{k}_{\mathrm{k}} \mathrm{n} 1 \#}\right)^{\mathrm{T}}+\mathrm{h}: \mathrm{c}: \tag{8}
\end{equation*}
$$

Here, $=(x ; y ; z)$, where the com ponents are Paulim atrioes and Eq.(8) yields the charge current operator if $\frac{1}{2}$ is replaced by a unit $m$ atrix $m$ ultiplied by the electronic charge $e=\sim$, where $e$ is the electronic charge (negative).

A $1 l$ currents $o w$ in the $y$ direction, penpendicular to the layers, and the com ponents of the vector $j$ correspond to transport of $x, y$, and $z$ com ponents of spin. The rate ofchange of $S_{n}$ in the sw itching $m$ agnet is given by

$$
\begin{equation*}
\mathrm{i} \sim \mathrm{~S}_{\mathrm{n}}=\left[\mathrm{S}_{\mathrm{n}} ; \mathrm{H}_{0}\right]+\left[\mathrm{S}_{\mathrm{n}} ; \mathrm{H}_{\text {an is }}\right] \tag{9}
\end{equation*}
$$

since the spin operator com $m$ utes with the interaction $H$ am iltonian $H$ int .
It is straightforw ard to show that

$$
\begin{equation*}
\left[S_{n} ; H_{0}\right]=i \sim\left(j_{n} 1 \quad \dot{h}_{n}\right) \tag{10}
\end{equation*}
$$

and

$$
\begin{equation*}
\left[\mathrm{S}_{\mathrm{n}} ; \mathrm{H}_{\text {an is }}\right]=\quad \mathrm{i} \sim\left(\mathrm{H}_{\mathrm{A}} \quad \mathrm{~S}_{\mathrm{n}}\right) \text {; } \tag{11}
\end{equation*}
$$

In a steady state, the $m$ agnetization is tim e-independent so that $\left\langle S_{\pi}\right\rangle=0$. Hence

$$
\begin{equation*}
<\dot{j}_{\mathrm{n} 1}><\dot{j}_{\mathrm{n}}>=\mathrm{H}_{\mathrm{A}}<\mathrm{S}_{\mathrm{n}}>: \tag{12}
\end{equation*}
$$

The left-hand side of Eq. (12) corresponds to the rate of transfer of spin angularm om entum to plane $n$ in the steady state. T hus E q.(12) show s explicitly how, in the steady state, this spin-transfer torque is balanced by the torque due to anisotropy elds. The concept of spin-transfer torque was rst introduced by Slonczew ski [11].

## KELDYSH FORMALISM

In this section we show how to calculate the spin current $\left\langle j_{n 1}>\right.$ and spin density $\left\langle S_{n}\right\rangle$ in the nonequilibrium steady state and verify that they are related by Eq.(12). To produce a spin-polarized current in the system we apply a bias $\mathrm{V}_{\mathrm{b}}$ betw een the polarizing m agnet and the lead. To use the K eldysh form alism
 hopping integral $T_{n}$ in 1 between planes $n \quad 1$ and $n$ is sw itched $O$. Then both sides of the system are in
equilibrium butwith di erent chem icalpotentials $L_{L}$ on the left and $R$ on the right, where $L_{R}=e V_{b}$. $T$ he interplane hopping is then tumed on adiabatically and the system evolves to a steady state. $T$ he cleavage plane, across which the hopping is initially sw itched $o, m$ ay be taken in either the spacer or sw itching layer or in the lead. F ig. 1 show $s$ the situation when the cleavage plane is betw een atom ic planes $\mathrm{n} \quad 1$ and n in the sw itching $m$ agnet. In principle, the $K$ eldysh $m$ ethod is valid for arbitrary bias $V_{b}$ but here we restrict ourselves to sm all bias corresponding to linear response. This is reasonable since for larger bias electrons would be in jected into the sw itching $m$ agnet far above the Ferm i level and $m$ any-body processes neglected here would be im portant. Furtherm ore, in $m$ etallic system $s$ the bias will never be large.


$$
\begin{equation*}
G_{R L}^{+}\left(t ; t^{0}\right)=i<c_{L}^{y}\left(t^{0}\right) C_{R}(t)>; \tag{13}
\end{equation*}
$$

where $R \quad\left(\mathrm{n} ; \quad ;{ }^{0}\right.$ ) and $\mathrm{L} \quad(\mathrm{n} 1 ; ~ ; ~)$, and we suppress the $k$ label. The therm al average in Eq. (13) is calculated for the steady state of the coupled system. Them atrix $G_{R L}^{+}$has dim ensions $2 m \quad 2 m$ where $m$ is the num ber of orbitals on each atom ic site, and is w ritten so that the $m \quad m$ upper diagonalblock contains $m$ atrix elem ents between " spin orbitals and the $m \quad m$ lower diagonalblock relates to \# spin. $2 \mathrm{~m} \quad 2 \mathrm{~m}$ hopping $m$ atrices $T_{L R}$ and $T_{R L}$ are written sim ilarly and in this case only the diagonalblocks are nonzero. If we denote $T_{L R}$ by $T$, then $T_{R L}=T^{Y} . W e$ also generalize the de nition of $s o$ that its com ponents are now direct products of the 22 Paulim atrioes $x ; y ; z$ and the $m \quad m$ unit $m$ atrix. The them alaverage of the spin current operator, given by Eq.(8), m ay now be expressed as

$$
\begin{equation*}
<j_{n 1}>=\frac{1}{2}_{k_{k}}^{X} \operatorname{Trf}\left[G_{R L}^{+}(t ; t) T \quad G_{L R}^{+}(t ; t) T^{y}\right] g: \tag{14}
\end{equation*}
$$

Introducing the Fourier transform $G^{+}(!)$of $G^{+}\left(t ; t^{0}\right)$, which is a function of $t \quad l$, we have

$$
\begin{equation*}
<j_{\mathrm{n} 1}>=\frac{1}{2}_{\mathrm{k}_{\mathrm{k}}}^{\mathrm{X}} \quad \frac{\mathrm{~d}!}{2} \operatorname{Trf}\left[G_{\mathrm{RL}}^{+}(!) \mathrm{T} \quad \mathrm{G}_{\mathrm{LR}}^{+}(!) \mathrm{T}^{\mathrm{y}}\right] \mathrm{g}: \tag{15}
\end{equation*}
$$

A gain, the charge current is given by Eq.(15) w ith $\frac{1}{2}$ replaced by the unit $m$ atrix $m$ ultiplied by $e=\sim$.
Sim ilarly, the totalspin angular mom entum on atom ic planes on either side of the cleavage plane, in the non-equilibrium state, is given by

$$
\begin{align*}
& <S_{n}>=\frac{1}{2}_{i \sim}^{X_{k}} \quad \frac{\mathrm{~d}!}{2} \operatorname{TrfG}_{R R}^{+}(!) g: \tag{17}
\end{align*}
$$

Follow ing $K$ eldysh $\overline{9}]\left[\begin{array}{l}-1\end{array}\right]$ [1] $]$, we now w rite

$$
\begin{equation*}
\mathrm{G}_{\mathrm{AB}}^{+}(!)=\frac{1}{2}\left(\mathrm{~F}_{\mathrm{AB}}+\mathrm{G}_{\mathrm{AB}}^{\mathrm{a}} \quad \mathrm{G}_{\mathrm{AB}}^{\mathrm{r}}\right) ; \tag{18}
\end{equation*}
$$

where the su ces $A$ and $B$ are either $R$ or $L . F_{A B}(!)$ is the Fourier transform of

$$
\begin{equation*}
\mathrm{F}_{\mathrm{AB}}\left(\mathrm{t} ; \mathrm{t}^{0}\right)=\mathrm{i}<\left[\mathrm{G}(\mathrm{t}) ; \mathrm{C}_{\mathrm{B}}^{\mathrm{y}}\left(\mathrm{t}^{0}\right)\right]> \tag{19}
\end{equation*}
$$

 of $\mathrm{G}^{\mathrm{a}}$ and $\mathrm{G}^{r}$ are interchanged and that in the G reen function $m$ atrix de ned by these authors $\mathrm{G}^{+}$and G should be interchanged.

C harge and spin current, and spin density, are related by Eqs.(15)-(17) to the quantities $\mathrm{G}^{\mathrm{a}}$, $\mathrm{G}^{\mathrm{r}}$, and $\mathrm{F}_{\mathrm{AB}}$. $T$ he latter are calculated for the coupled system by starting $w$ ith decoupled left and right system s , each in equilibrium, and tuming on the hopping betw een planes $L$ and $R$ as a perturbation. Hence, we express $G^{a}$,
$G^{r}$, and $F_{A B}$ in term sof retarded surface $G$ reen functions $g_{L} \quad G_{L}, g_{R} \quad G_{R}$ for the decoupled equilibrium system. The nal result for the spin angular $m$ om entum on plane $n$ to the right of the cleavage plane is

$$
\begin{equation*}
<S_{n}>=<S_{n}>_{1}+<S_{n}>_{2} ; \tag{20}
\end{equation*}
$$

where the tw o contributions to the spin angularm om entum $\left\langle S_{n}>_{1} \text { and }<S_{n}\right\rangle_{2}$ are given by

$$
\begin{align*}
& <S_{n}>_{1}=\frac{\sim}{4}_{\mathrm{k}_{\mathrm{k}}}^{\mathrm{Z}} \mathrm{~d}!\operatorname{Im} \operatorname{TrfA} g_{R} \quad \mathrm{~g}[\mathrm{f}(!\quad \mathrm{L})+\mathrm{f}(!\quad \mathrm{R})]  \tag{21}\\
& <S_{n}>_{2}=\frac{\sim}{2}_{k_{k}}^{X} d!\operatorname{Im} \operatorname{Trf}\left(A \quad \frac{1}{2}\right) B g_{R}^{y} \quad g[f(!\quad L) \quad f(!\quad R)]: \tag{22}
\end{align*}
$$

 potential and $L \quad R_{R}=e V_{b}$. To obtain $\left\langle S_{n} l_{1}\right\rangle$, de ned by Eq.(16), wem ust interchange $L$ and $R$, and $T$ and $T^{y}$, everyw here in Eq.(20)-(22). In the linear-response case of $s m$ all bias which we are considering, the Ferm i functions in Eq. (22) are expanded to rst order in V. H ence the energy integral is avoided, being equivalent to $\mathrm{m} u$ ultiplying the integrand by $\mathrm{eV}_{\mathrm{b}}$ and evaluating it at the com m on zero-bias chem icalpotential 0 .
As show $n$ in $F$ ig.1, the $m$ agnetization $P$ of the polarizing ferrom agnet is assum ed to be $x e d$ in the ( $z ; x$ ) plane and $m$ akes an angle w the the $z$ axis, which is the direction of the uniaxial anisotropy eld in the sw itching magnet. W hen a bias is applied, spin-polarized current ow sthrough the switching magnet and exerts a torque on its $m$ agnetization. This torque is in com petition $w$ ith the torque due to the anisotropy
eld and causes the spin $<\mathrm{S}_{\mathrm{n}}>$ in a given atom ic plane n to deviate from the anisotropy axis. In the steady state $\left\langle S_{n}\right\rangle$ settles in a de nite direction speci ed by the angles ${ }_{n}$, $n$ show $n$ in $F$ ig.1. To determ ine these angles, we assum e the exchange eld $n$ in plane $n$ is in the direction ( $n ; n$ ) and apply the self-consistency condition

$$
\begin{equation*}
\mathrm{n}<\mathrm{S}_{\mathrm{n}}>=0: \tag{23}
\end{equation*}
$$

$T$ his condition guarantees that the localm agnetization is in the direction of the exchange eld, as it should be in the unrestricted $H$ artree Fock approxim ation $m$ entioned in Sec.1. A swith anisotropy elds, the exchange eld $n$ is de ned as an angular frequency so that $\sim{ }_{n}$ is the energy to reverse the spin on plane $n$. M ore precisely, the spin-dependent part of the on-site energy on plane $n$ is given by $\quad(1=2) \sim\left(H_{A}+\quad n\right)$ : We assume that $j n$ jalwaystakes its bulk value.

Follow ing the $m$ ethod outlined for obtaining Eq.(20), sim ilar expressions in term s of retarded surface $G$ reen functions $m$ ay be obtained for the spin currents $<j_{n 1}>$ and $<j_{n}>$. W riting again $<j_{n}>=<j_{n}>_{1}$ $+\left\langle j_{n}\right\rangle_{2}$, we obtain

$$
\begin{align*}
& <j_{n 1}>_{1}=\frac{1}{4}_{k_{k}}^{X} \operatorname{d!ReTrf}(B \quad A) \quad g\left[f\left(\begin{array}{lll}
\mathrm{B} & \mathrm{~L}
\end{array}\right)+\mathrm{f}\left(\begin{array}{ll}
! & \mathrm{R}
\end{array}\right)\right]  \tag{24}\\
& <j_{n 1}>_{2}=\frac{1}{2}_{k_{k}}^{X} \quad d!\operatorname{ReTrf}\left[g_{L} T A B g_{R}^{y} T^{Y} \quad A B+\frac{1}{2}(A+B)\right] g[f(!\quad L) \quad f(!\quad R)]: \tag{25}
\end{align*}
$$

By considering the changes in $g_{\mathrm{L}}, g_{R}$ when the cleavage plane is $m$ oved one atom ic plane to the right, it is straightforw ard to show that

$$
\begin{equation*}
<j_{\mathrm{n} 1}><\dot{j}_{\mathrm{n}}>=\left(\mathrm{H}_{\mathrm{A}}+\mathrm{n}_{\mathrm{n}}\right)<\mathrm{S}_{\mathrm{n}}>: \tag{26}
\end{equation*}
$$

This equation holds for a steady state $w$ th anbitrary exchange elds $n$ which do not necessarily satisfy the self-consistency condition (23). W hen the self-consistency condition (23) is satis ed, we recover the steady-state result

$$
\begin{equation*}
<j_{\mathrm{n} 1}><\dot{\eta}_{\mathrm{h}}>=\mathrm{H}_{\mathrm{A}}<\mathrm{S}_{\mathrm{n}}> \tag{27}
\end{equation*}
$$

which was derived earlier Eq.(12)] purely from considerations of the spin-rotationalsym m etry ofthe electronelectron interactions. This veri es the consistency of the $K$ eldysh form alism com bined w ith the unrestricted H artree Fock approxim ation.

It follow s from Eqs.(26) and (27) that all com ponents of spin current are conserved w ithin the spacer and lead, where $H_{A}=0 ; n_{n}=0$, with or $w$ ithout self-consistency. Furtherm ore, it follow s from Eq.(27) that in the self-consistent steady state the com ponent of spin current in the direction of the anisotropy eld $H_{A}$ is conserved throughout the system, as of course is the charge current. If Eq.(27) is sum m ed over allplanes in the sw itching $m$ agnet, we obtain

$$
\begin{equation*}
<j_{\text {spacer }}><\dot{j}_{\text {lead }}>=H_{\mathrm{A}}<\mathrm{S}_{\text {tot }}>; \tag{28}
\end{equation*}
$$

$w$ here $<j_{\text {spacer }}>,<j_{\text {lead }}>$ are the spin currents in the spacer and lead, respectively, and $<S_{\text {tot }}>$ is the totalspin angularm om entum of the sw itching $m$ agnet. $T$ his show $s h o w$ the total spin transfer torque acting on the sw itching $m$ agnet is balanced by the torque exerted by the anisotropy eld on the totalm om ent.

W e have separated in Eq. (20) the spin angularm om entum $<S_{n}>$ into two parts $<S_{n}>_{1}$ and $<S_{n}>{ }_{2}$. It is clear that $<S_{n}>_{2}$ is proportional to the applied bias $V_{b}$ to the rst order and for zero bias ( $L={ }_{R}$ ) only $<\mathrm{S}_{\mathrm{n}}>_{1}$ rem ains. The spin transfer torque $<j_{\mathrm{n}}><\dot{\eta}_{1}>$ sim ilarly splits into two parts (Eqs.(24),(25)) in such a way that Eq.(26) holds for each com ponent separately:

$$
\begin{equation*}
<j_{n 1}>_{i}<\dot{j}_{n}>_{i}=\left(H_{A}+{ }_{n}\right) \quad<S_{n}>_{i} ; i=1 ; 2: \tag{29}
\end{equation*}
$$

Only the rst part $<\dot{j}_{1}>_{1}<\dot{h}_{1}>_{1}$ is nonzero at zero bias. It corresponds to spin currents which $m$ ediate exchange coupling, either betw een the tw o $m$ agnets across the spacer or betw een atom ic planes in the $s w i t c h i n g m$ agnet. C onsequently, at zero bias the spin current in the lead is zero. It is easy to verify that the expressions for interlayer exchange coupling_ derived here, using the K eldysh form alism, agree precisely $w$ ith those obtained earlier by other $m$ ethods [ 141$]$.
$T$ he results of this section show the great advantage of the $K$ eldysh form alism, even w thin the linear response regim e. Spin currents at zero bias, corresponding to exchange coupling, transport spin and particle currents, and spin densities are all calculated in a uni ed way. Relationships betw een these quantities, such as Eq. (29), are then easily derived. In the standard linear response theory of $K$ ubo zero-bias quantities cannot be calculated and di erent response functions would have to be introduced for calculating currents and spin density response at nite bias.

## APPLICATION TOA SW ITCHING MONOLAYER

In the general theory outlined in Sec. 3 the steady-state spin orientation of each atom ic plane $n$ of the $s w$ itching $m$ agnet $m$ ust be determ ined self-consistently. In this section we rst consider the sim plest case of a single orbital on each site and when the sw itching $m$ agnet is a single atom ic plane. In this case there is no interplane exchange coupling in the sw itching $m$ agnet to consider and we assum e that the spacer is su ciently thick for the zero-bias exchange coupling betw een the two ferrom agnets to be negligible. For a given bias $\mathrm{V}_{\mathrm{b}}$, the direction ( 0 ; 0 ) of the steady-state orientation of the $s w$ itching $m$ agnet $m$ om ent < $S>$ is determ ined self-consistently from Eq. (23) w ith the cleavage plane im m ediately to the left of the sw itching plane so that $\left\langle S_{n}\right\rangle=\langle S\rangle$. It is convenient to determ ine ( $0 ; 0$ ) in two steps. The rst step locates a 'universal path' on a unit sphere, independent of $\mathrm{V}_{\mathrm{b}}$, on which the self-consistent solutions for any given $\mathrm{V}_{\mathrm{b}}$ $m$ ust lie. In the second step the bias $V_{b}$ required to stabilize the $m$ agnetization in a given direction ( 0 ; 0 ) is determ ined as a function of 0 , say. To establish this program, we write Eq. (23) as

$$
\begin{equation*}
\left(\mathrm{H}_{\mathrm{A}}+\quad\right)<\mathrm{S}>=\mathrm{H}_{\mathrm{A}}<\mathrm{S}>; \tag{30}
\end{equation*}
$$

where is the exchange eld of the switching layer in the direction ( $0 ; 0$ ). Splitting $<S>$ into two parts as in Eq. (20), this becom es

$$
\begin{equation*}
\left(\mathrm{H}_{\mathrm{A}}+\right)<\mathrm{S}>_{1}+\left(\mathrm{H}_{\mathrm{A}}+\right)<\mathrm{S}>_{2}=\mathrm{H}_{\mathrm{A}}<\mathrm{S}>: \tag{31}
\end{equation*}
$$

H ence using Eq. (29) we have

$$
\begin{equation*}
<j_{\text {spacer }}>_{1}<\dot{j}_{\text {lead }}>_{1}+<j_{\text {spacer }}>_{2}<\dot{j}_{\text {lead }}>_{2}=H_{A}<S>: \tag{32}
\end{equation*}
$$

The rst tw o term s on the left correspond to exchange coupling torque which, as discussed above, is assum ed to be negligible com pared w th the anisotropy torque. This is justi ed for thick spacers since the interlayer exchange coupling tends to zero as the spacer thickness tends to in nity. The last two term s on the left correspond to the spin transfer torque $T$, which is proportional to bias $\mathrm{V}_{\mathrm{b}}$, and the right-hand side of q . (32) is $T_{A}$, where $T_{A}$ is the torque exerted by the anisotropy eld on the sw itching $m$ agnet. $W$ e shall see that, in contrast to the exchange coupling torque, $T$ rem ains nite as spacer thickness tends to in nity. Hence

$$
\begin{equation*}
\mathrm{T}=\left\langle j_{\text {spacer }}>_{2}<j_{\text {lead }}>_{2}=\mathrm{H}_{\mathrm{A}}<\mathrm{S}>=\mathrm{T}_{\mathrm{A}}\right. \tag{33}
\end{equation*}
$$

and, in particular,

$$
\begin{equation*}
T H_{A}=0: \tag{34}
\end{equation*}
$$

$T$ hebias $V_{b}$ now cancels and this equation determ ines the universalpath described above. Eq.(33) determ ines the bias required to stabilize any particular point on this path of possible steady states.
W e conclude this section w ith one exam ple in which, for sim plicity, we retain only uniaxial anisotropy, this eld being chosen in the $z$ direction. $W$ e use a single-orbitaltight-binding $m$ odelwhose lattioe is taken to be sim ple cubic w ith layering in the (010) direction. T he nearest-neighbor hopping param eter $t$ is taken to be the sam e throughout the system. T he on-site energy in the spacer and lead is taken as $\mathrm{V}_{\text {sp }}$, the zero of energy being at the com $m$ on $F e m$ i level for zero bias. In this exam ple the on-site energy $V_{s p}$ is also taken for $m$ ajority spin in the ferrom agnets (perfect $m$ atching in the $m$ ajority-spin channel). The on-site energy for $m$ inority spin in the ferrom agnets is taken as $V_{s p}+\sim$, where $\sim$ is the exchange splitting. The $m$ atching of spacer and $m$ a jority spin bands is sim ilar to the situation in $\mathrm{Co} / \mathrm{Cu}$. W e take $\mathrm{V}_{\mathrm{sp}}=2: 3 ; \sim=0: 7$ in units of $2 t$. Furtherm ore, we take the uniaxial eld param eter $H_{u 0}=1: 86 \quad 10^{10} \mathrm{sec}^{1}$ which corresponds to a eld of $0: 106 \mathrm{~T}$. W e also take a general value $=2$ radians of the angle betw een the polarizing $m$ agnet m om ent and the direction of the uniaxial anisotropy axis of the $s w$ itching $m$ agnet. To determ ine the torque $T$ which appears in Eq.(34) for the universalpath, we need to calculate the $G$ reen functions $g_{L}$; $g_{R}$ which are required in Eq.(25). This is done by standard adlayering $m$ ethods described previously [ $\left[\begin{array}{l}-1 \\ 1\end{array}\right]$. At this stage, the anisotropy eld is included in the calculation of all the $G$ reen functions. Fig 2 show $s$ the calculated universal path of versus for the speci ed param eters. The bias $V_{b}$ required to yield a steady-state

$m$ agnetization at a given point of this path is plotted as a function of in $F$ ig. 3, where we have assum ed the band width $12 t=6 \mathrm{eV}$. Positive bias corresponds to a drop in voltage betw een the polarizing $m$ agnet and the lead. The correspondence betw een the two curves in Fig. 2 and $F$ ig. 3 is indicated by letters $P$ and $Q$. The discussion of stability of these steady states and the interpretation of F ig 3 is postponed to section 7. $T$ he $m$ ethod of calculating steady states used in this section becom es more com plicated when the sw itching $m$ agnet contains several atom ic planes since the $m$ om ents $\left\langle S_{n}\right\rangle$ of all planes $m$ ust be determ ined selfconsistently. This entails the inclusion of the exchange sti ness between atom ic planes of the switching m agnet which is contained in Eq. (29) with $i=1$. To address this problem, we introduce in the next section the simpli cations required to derive from rst principles the convenient 'standard $m$ odel' used by previous authors $\left[\begin{array}{ll}{[1]} \\ 1\end{array}\right]$ [


F IG . 3: B ias $V_{b}$ required to stabilize the sw itching $m$ agnet $m$ om ent at an angle on the universal path.

THESTANDARD MODEL

In the $K$ eldysh $m$ ethod used above it is essential to include the anisotropy eld $H_{A}$ in the $H$ am iltonian to obtain a non-trivial steady state. In the absence of $H_{A}$ it follows from Eq. (27) that in the steady state all com ponents of spin current are conserved everyw here so that there are no spin-transfer torques. H ence the only steady state is the trivial one in which the sw itching magnet is aligned parallel or antiparallel to the polarizing $m$ agnet. P revious authors [1] $\left[\begin{array}{ll}1 /[1]\end{array}\right]$ did not consider a steady state but calculated spin-transfer torque as a one-electron problem w th the exchange elds of the polarizing and sw itching magnets at a xed assum ed angle. In a second independent step, these authors [ill $]$ [ the torque due to anisotropy eld in the context of a Landau-Lifhitz equation. This approach is what we call the standard $m$ odel (SM). In this section we show how to arrive at the $S M$ by $m$ aking som e sim plifying approxim ations in our self-consistent approach.
$W$ e begin $w$ th the $m$ onolayer sw itching $m$ agnet ofSec.4. In Eq.(33) the spin-transfer torque $T$ is calculated in the presence of $H_{A}$ and the spin $\langle S>$ is the self-consistent $m$ om ent. To obtain the SM we m ust neglect $H_{A}$ in the calculation of $T$ and replace $<S>$ by its nonself-consistent value in the direction of the assum ed exchange eld of the switching $m$ agnet. These approxim ations are both reasonable provided the exchange
eld is much stronger than the anisotropy eld, which is satis ed for a ferrom agnet such as Co. This follow s since the $G$ reen functions which determ ine both $T$ and $\langle S\rangle$ depend on the total eld $+H_{A}$.Thus in the SM the spin-transfer torque is calculated as a function of the angle betw een the $m$ agnetizations $w$ thout solving the self-consistency problem. Furthem ore, equating it to the anisotropy torque as in Eq.(33) is equivalent to calculating a steady state of the Landau-屯ifshitz equation. The justi cation of the SM for a $s w$ itching $m$ agnet $w$ ith $m$ ore than one atom ic plane is $m$ ore subtle.

The self-consistency condition (23) m ust be satis ed for each plane in the $s w$ itching $m$ agnet. It $m$ ay be written [c.f. Eq.(30) for the $m$ onolayer]

$$
\begin{equation*}
\left(\mathrm{H}_{\mathrm{A}}+\mathrm{n}_{\mathrm{n}}\right)<\mathrm{S}_{\mathrm{n}}>=\mathrm{H}_{\mathrm{A}}<\mathrm{S}_{\mathrm{n}}> \tag{35}
\end{equation*}
$$

and, using again $\left\langle\mathrm{S}_{\mathrm{n}}\right\rangle=\left\langle\mathrm{S}_{\mathrm{n}}>_{1}+\left\langle\mathrm{S}_{\mathrm{n}}>_{2}\right.\right.$ and Eq.(29), we obtain

$$
\begin{equation*}
<j_{\mathrm{n} 1}>_{1}<\dot{\eta}_{1}>_{1}+\left\langle\dot{j}_{\mathrm{n} 1}>_{2}<\dot{\eta}_{\mathrm{n}}>_{2}=\mathrm{H}_{\mathrm{A}} \quad<\mathrm{S}_{\mathrm{n}}>:\right. \tag{36}
\end{equation*}
$$

The rst two term scontain the interlayer exchange coupling, which is neglected as in the monolayer case, and interplane exchange coupling $w$ ith in the sw itching $m$ agnet. To clarify the argum ent, we w rite notionally this last contribution in term s of localexchange sti ness $D_{n}$ betw een atom ic planes $n \quad 1$ and $n$. Hence from Eq.(36)

$$
\begin{equation*}
<\dot{j}_{\mathrm{n} 1}>_{2}<\dot{\eta}_{\mathrm{n}}>_{2}=\mathrm{H}_{\mathrm{A}}<\mathrm{S}_{\mathrm{n}}>+\mathrm{D}_{\mathrm{n} 1}\left(\mathrm{~S}_{\mathrm{n} 1} \quad \mathrm{~S}_{\mathrm{n}}\right) \quad \mathrm{D}_{\mathrm{n}}\left(\mathrm{~S}_{\mathrm{n}} \quad \mathrm{~S}_{\mathrm{n}+1}\right): \tag{37}
\end{equation*}
$$

On sum $m$ ing over all planes $n$ in the switching $m$ agnet the intemal exchange coupling torques cancel and
we have

$$
<j_{\text {spacer }}>_{2}<j_{\text {lead }}>_{2}=H_{A} \quad X \quad<S_{n}>:
$$

In the fully self-consistent solution of Eq. (35) the exchange eld $n$ is parallelto the localm om ent $<S_{n}>$ but the $n$ are not collinear. To proceed to the SM wemust assum e that all the $n$ used to calculate the spin-transfer torque on the left of Eq. (38) are equal, to , say. Furthem ore, we assum e, as in the case of the $m$ onolayer, that we can neglect $H_{A}$ in the calculation of the spin-transfer torque and that all $<S_{n}>$ are in the direction $w$ ith $m$ agnitude equal to the ground state $m$ om ent. In $m$ aking the approxim ation
n we have failed to satisfy Eqs. (37) individually as is required for full self-consistency.
To show that this is not serious for a ferrom agnet such as Co, consider the follow ing argum ent. If we use the uniform value of determ ined from Eq.(38), as described, to calculate the spin-transfer torque in Eq.(37) and assume all $<S_{n}>$ are in the direction of, the last two term sofeq.(37) are zero and the equations are far from satis ed. H ow ever, since the exchange sti ness constants $\mathrm{D}_{\mathrm{h}}$ of a ferrom agnet such as C o are large one need only introduce sm all deviations of $n$ from the uniform, and consequently sm all deviations of $\left\langle S_{n}\right\rangle$ from uniform ity, to satisfy the self-consistent equations (37). This is true because the spin-transfer and anisotropy torques are insensitive to these sm all deviations. The ability of the SM to sim ulate the fully self-consistent solution accurately has been veri ed num erically for a switching magnet w ith two atom ic planes using the single-orbitalm odel of Sec.4.

## TW O COMPONENTSOFTHESPIN-TRANSFERTORQUE INTHESTANDARDMODEL

In the calculation of the spin-transfer torque $T$ w ithin the standard $m$ odel the anisotropy eld is neglected so that $T$ depends only on the angle between the $m$ agnetization $P$ of the polarizing $m$ agnet and the assum ed exchange eld of the sw itching magnet. As in F ig.1, the m agnetization P of the polarizing $m$ agnet is in the $(z, x)$ plane, $m$ aking an angle $w$ th the $z$ axis, and, for convenience, we choose the exchange eld of the sw itching $m$ agnet to be in the $z$ direction so that $\quad=$. The torque $T$ in the $S M$ is given by

$$
\begin{equation*}
T=\left\langle j_{\text {spacer }}>_{2}<j_{\text {lead }}>_{2}\right. \tag{39}
\end{equation*}
$$

where the right-hand side is related to the totalbias-induced spin $S_{2}={ }^{P}{ }_{n}<S_{n}>{ }_{2}$ by Eq.(29), summed over $n$, with $H_{A}$ neglected and $n=$. It follows that

$$
\begin{equation*}
\mathrm{T}=\quad \mathrm{N}_{\mathrm{n}}<\mathrm{S}_{\mathrm{n}}>_{2}=\quad \mathrm{S}_{2}: \tag{40}
\end{equation*}
$$

Here, $\left\langle S_{n}\right\rangle_{2}$ is given by Eq. (22) with $H_{A}$ neglected in the $G$ reen functions $g_{L}$, $g_{R}$. The three com ponents of $S_{2}=\left(S_{2 x} ; S_{2 y} ; S_{2 z}\right)$ are related to the three Paulim atrioes $x ; y ; z$ in Eq.(22). C learly, from Eq.(40) the $z$ com ponent of torque is zero so that we can w rite

$$
\begin{equation*}
\mathrm{T}=\left(\mathrm{T}_{\mathrm{x}} ; \mathrm{T}_{\mathrm{y}} ; 0\right): \tag{41}
\end{equation*}
$$

The 'in-plane' com ponent $T_{k}=T_{x}$, where 'in-plane' refers to the $\left(z_{r} x\right)$ plane containing $P$ and, is given by $\mathrm{T}_{\mathrm{k}}=\mathrm{S}_{2 \mathrm{y}}$ and the 'out-of-plane' com ponent $\mathrm{T}_{?}=\mathrm{T}_{\mathrm{y}}$ is given by $\mathrm{T}_{\mathrm{?}}=\mathrm{S}_{2 \mathrm{x}}$. The quantities

eld. These spin com ponents are referred to by previous authors '[1.5], '[1' 1 ] as 'spin accum ulation'. In the self-consistent steady-state treatm ent of Sec. 4 such deviations do not occur because the exchange eld is alw ays in the direction of the localm om ent. In our view, tim e-independent spin accum ulation $S_{2 x}, S_{2 y}$ in the ferrom agnet is a non-physicalconcept which, how ever, wem ay de ne form ally as the ratio oftorques $\mathrm{T}_{\mathrm{k}}$, $T_{\text {? }}$, to the exchange eld. It is rem arkable that, as shown in Sec.5, the SM in which this concept arises provides a convenient and frequently accurate $m$ ethod for calculating spin-transfer torque. $T$ im e-dependent spin accum ulation in the ferrom agnet in a non-steady state could be a valid concept. H ow ever, these tim edependent spins would produce tim e-dependent exchange elds which would excite the whole spin system. $T$ his w ould require a $m$ any-body treatm ent going beyond the unrestricted $H$ artree $F$ ock approxim ation which
is adequate for the steady state. Spin accum ulation $\left\langle S_{x}\right\rangle,\left\langle S_{y}\right\rangle,\left\langle S_{z}\right\rangle$ proportional to the bias exists in the spacer even in the steady state and has real physical signi cance. Calculation of this e ect will be published in a succeeding paper.

The spin transfer torque can be calculated either directly from Eq.(39) or from Eq.(40). H ow ever, the latter would require calculating $\left\langle S_{n}\right\rangle_{2}$ for each atom ic plane of the sw itching $m$ agnet so that the direct $m$ ethod is obviously preferable.

W e begin with an exactly solvable one-band model which we can connect w ith previous work [1] [1]. This m odel is related to the one described at the end of Sec. 4 , where the sw itching $m$ agnet is a single atom ic plane and there is perfect $m$ atching betw een the spacer band and the $m$ a jority spin bands in both ferrom agnets. To obtain analytical results in this rst exam ple, we also assum e that the exchange splitting ! 1 both in the polarizing and sw itching $m$ agnets. In fact, once the bottom of the $m$ inority-spin band is well above the Ferm i level, the results are rather insensitive to the $m$ agnitude of. Such a system is som etim es referred to as a halfm etallic ferrom agnet and is the rst case considered by Slonczew ski in his original paperi_[]. In the lim it ! 1 the $S M \mathrm{~m}$ odel is exact since the $m$ om ent of the $s w i t c h i n g m$ agnet cannot deviate from the exchange eld and the self-consistency condition (23) is autom atically satis ed. W e, therefore, calculate the spin-transfer torque in the absence of anisotropy eld. C learly, ow ing to the in nite exchange splitting, the only spin current in the lead corresponds to the $z$ com ponent of spin and the $z$-spin current is equal to the charge current ( $m$ ultiplied by $\sim=2 e$ ). It turns out in this $m$ odel that the $y$-spin current in the spacer, which is equal to the torque $T_{\text {? }}$ since the corresponding current in the lead is zero, vanishes. T hus only Slonczew skitorque $\mathrm{T}_{\mathrm{k}}$ survives and is given by

$$
\begin{equation*}
T_{k}=e_{x} \frac{e V}{8}_{k_{k}}^{X} \frac{t^{2}\left(g_{0} g\right)^{2} \sin }{\left.j 1 g_{0}(a+b \cos )\right\}^{2}}: \tag{42}
\end{equation*}
$$

Here, $g_{0}=g_{0}\left(k_{k} ; 0\right)$ is the $m$ a jority spin surface $G$ reen function for the sem i-in nite ferrom agnet, or equivalently for the sem i-in nite ferrom agnet w th an overlayer of the $m$ atching spacer. The $G$ reen function $g$ is evaluated at energy ! = 0 , the com $m$ on Ferm ilevel of the unbiased system. A lso, $t$ is the hopping param eter introduced in Sec. 4 and a and b are given by

$$
\begin{equation*}
a=\frac{1}{2}\left(g_{0}+A_{N}\right) ; b=\frac{1}{2}\left(g_{0} \quad A_{N}\right) ; \tag{43}
\end{equation*}
$$

where $\left.A_{N}=\sin N k_{\text {? }} d=t \sin (N+1) k_{\text {? }} d\right] w$ th

$$
\begin{equation*}
k_{?} d=\cos ^{1}\left[\left(N_{s}^{\prime \prime}+2 t\left(\operatorname{cosk}_{x} d+\operatorname{cosk}_{y} d\right)\right)=2 t\right] \tag{44}
\end{equation*}
$$

and $k_{k}=\left(k_{x} ; \mathrm{k}_{\mathrm{y}} ; 0\right) ; \mathrm{d}$ is the interatom ic distanœ, N is the num ber of atom ic planes in the spacer, and $\mathrm{V}_{\mathrm{s}}{ }^{"}$ is the on-site potential in the $m$ a jority-spin band of the $s w$ itching $m$ agnet. $T$ he corresponding expression for the charge current is very sim ilar and we nd that

$$
\begin{equation*}
\mathrm{T}_{\mathrm{k}}=\frac{\sim}{2 j \mathrm{jej}} \tan (=2) \quad(\text { charge current }): \tag{45}
\end{equation*}
$$

This is precisely the Slonczew ski result for the analogous parabolic band model. It should be noted that the torque $T_{k}$ goes to zero for ! since the charge current for a halfm etallic $m$ agnet contains a factor $1+\cos$.
$T$ he interesting result that $T_{\text {? }}=0$ for this $m$ odel $m$ ay be traced to an ective re ection sym $m$ etry of the system about a plane at the center of the spacer. A lthough the present system appears asym $m$ etric the in nite exchange splitting $m$ akes it equivalent to a sym $m$ etric system $w$ ith sem i-in nite sw itching $m$ agnet. $M$ ore generally, we nd, certainly for a one-band $m$ odelw ith arbitrary param eters, that the $y$-spin com ponent of the spin current in the spacer alw ays vanishes for a system w ith re ection sym $m$ etry. In general, how ever, the $y$-spin current in the lead is non-zero so that $T_{\text {? }} 0$ even for a sym $m$ etric system. $T$ he result $T_{\text {? }}=0$ for the above $m$ odel is, therefore, a very special one due to the artefact of a very large exchange splitting in the ferrom agnets.

In the second set of exam ples we consider several cases, $w$ thin the one-band $m$ odel, where the exchange splittings in the ferrom agnets are nite. Simple form ulas, such as Eq. (42), for the torques are no longer

TABLE I: Param eters for one-band $m$ odels. $V_{p}^{\prime \prime}, V_{p}^{\#}$ are on-site potentials for $m$ ajority and $m$ inority spin in the polarizing $m$ agnet; $\mathrm{V}_{s}$ " $\mathrm{V}_{s}^{\#}$ are on-site potentials for m ajority and m inority spin in the sw itching m agnet; $\mathrm{V}_{s p}$ is the on-site potential in the spacer and the lead; $\mathrm{N}, \mathrm{M}$ are the numbers of atom ic planes in the spacer and sw itching $m$ agnet, respectively.

| case | $\mathrm{V}_{\mathrm{p}}{ }^{"}$ | $\mathrm{~V}_{\mathrm{p}}^{\#}$ | $\mathrm{~V}_{\mathrm{sp}}$ | $\mathrm{V}_{\mathrm{s}}{ }^{\text {" }}$ | $\mathrm{V}_{\mathrm{s}}{ }^{\#}$ | N | M |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| (a) | 2.3 | 3.0 | 2.3 | 2.3 | 5.0 | 20 | 1 |
| (b) | 2.3 | 3.0 | 2.3 | 2.3 | 3.0 | 20 | 1 |
| (c) | 2.3 | 3.0 | 2.3 | 2.8 | 3.0 | 20 | 1 |
| (d) | 2.1 | 3.0 | 2.8 | 2.1 | 5.0 | 20 | 1 |
| (e) | 2.3 | 3.0 | 2.3 | 2.8 | 3.0 | 20 | $1-10$ |

available and they m ust be calculated num erically. In all the exam ples the calculated torques are per surface atom. In all cases, we retain the geom etry of the rst exam ple. Table I lists the param eters for all the cases considered.
A llpotentials in T able 1 are in units of 2 t and the Ferm ienergy $0=0$.
$F$ igure 4 (a) show sthe calculated torques $T_{k}$ per surface atom (in units of $\mathrm{eV}_{\mathrm{b}}$ ) as a fiunction of the angle for the $m$ odels $w$ th param eter sets (a)-(d) of Table 1. In case (a) $T_{k}$ dom inates, as expected from the


F IG . 4: D ependence of the spin-transfer torques $T_{k}$ (a) and $T_{\text {? }}$ (b) on the angle for the $m$ odelwith param eter sets (a)-(d) of $T$ able 1. The torques are in units of $\mathrm{eV}_{\mathrm{b}}$.
large exchange splitting $V_{s} " \quad V_{s}^{\#}$ in the switching $m$ agnet which approaches the in nite exchange splitting of our rst exactly solvable $m$ odel. The angular dependence ofboth torques is clearly dom inated by a sin factor (c.f. Eq.(42)) although som e distortions are apparent. In case (b) $T_{k}$ and $T_{\text {? }}$ are of alm ost equal strength. This is case where the tw oferrom agnets are of the sam em aterial and the bottom of the m inority spin band is exactly at the Ferm i level. This sim ulates well the situation in Co/Cu and we shall see presently that in realistic calculations for this system the torques $\mathrm{T}_{\mathrm{k}}$ and $\mathrm{T}_{\text {? }}$ are again sim ilar in m agnitude. The param eters of case (b) were used previously in Sec. 4 as an exam ple of a fully self-consistent calculation of steady states. In case (c) $T_{\text {? }}$ is larger than $T_{k}$. It is interesting that this occurs for sm aller exchange splitting in the sw itching ferrom agnet. In cases (b) and (c) the angular dependence of the torques is hardly distorted from the $\sin$ form. In cases (a), (b), (c) the tw o torques $T_{k}, T_{\text {? }}$ have the sam e sign. In case (d) they have opposite sign and alm ost equalm agnitude. In exam ples (a)-(d) the $s w$ itching $m$ agnet consists of one atom ic plane. In case (e) shown in Fig. 5 we use the sam e param eters as in case (c) but the num ber of atom ic planes in the sw itching $m$ agnet varies betw een 1 and 10 and the angle $=2$. It can be seen from $F$ ig. 5 that, contrary to popular belief, the out-of-plane torque $T_{\text {? }}$ dom inates over $T_{k}$ for sm all thicknesses of the $s w$ itching $m$ agnet and rem ains $50 \%$ of $T_{k}$ at $M=10$ at. planes. For all thicknesses of the $s w$ itching $m$ agnet, $T_{k}$ and $T_{\text {? }}$ have the sam e sign. W e have already seen in case ( d ) that this is not alw ays the case.

So far we have kept the num ber of atom ic planes in the spacer at 20 but we $m$ ust now highlight an


F IG . 5: D ependence of the spin-transfer torque $T_{k}$ and $T_{\text {? }}$ on the thickness of the sw itching $m$ agnet $M$ for $=2$ and the param eter set (c) of T able 1. T he torques are in units of $\mathrm{eV}_{\mathrm{b}}$.
im portant and surprising result conceming the dependence of torque on $N$. In $F$ ig. 6 we show the torques for the param eter set (b) and $==2$ plotted as functions of $N$. It is clear that they both oscillate but


F IG. 6: Dependence of the spin-transfer torque $T_{k}$ and $T_{\text {? }}$ on the thickness of the spacer $N$ for $=2$ and the param eter set (b) of $T$ able 1. $T$ he torques are in units of $\mathrm{eV}_{\mathrm{b}}$.
tend to constant values as N ! 1 in our ballistic lim it. In zero bias all spins of the system lie in the $(z, x)$ plane and it is, therefore, not surprising that when charge current ow $s$ in nonzero bias there are nite $z$-sp in and $x$-spin currents for arbitrary spacer thickness. The constant value of $y$-spin current as $N!1$, this being associated $w$ th $T_{\text {? }}, m$ ay seem $m$ ore surprising since there is no $y$-spin density in zero bias. $O f$ course, for 0 , there is a $y$-spin current even in zero bias corresponding to interlayer exchange coupling, but thise ect is not associated w ith charge transport and decays as $1=\mathrm{N}^{2}$ w ith increasing spacer thickness. $T$ he relations $T_{k}=S_{2 y}, T_{?}=S_{2 x}$ derived in the beginning of this section w ith in the standard m odel show that bias-induced in-plane spin density is related to out-of-plane torque and vice versa. It is, therefore, inevitable that both torques w ill exist.

As a nal exam ple of these spin-transfer torque calculations we consider a fully realistic multi-onbital $m$ odel of ficc $\mathrm{Co} / \mathrm{Cu}$ (111) w ith tight-binding param eters tted to the results of rst-principles band structure calculations, as described previously [ $1 \overline{2}$ 'ㄱ]. Referring to F ig.1, the polarizing $m$ agnet is a sem i-in nite slab
 $M=1$ and 2 , and the lead is sem i-in nite $C u$. $F$ igure 7 (a), (b) show sthe angular dependences of $T_{k}, T_{\text {? }}$ for the cases $M=1$ and $M=2$, respectively. For the $m$ onolayer sw itching $m$ agnet, the torques $T_{\text {? }}$ and $T_{k}$ are equal in $m$ agnitude and they have the opposite sign. How ever, for $M=2$, the torques have the sam $e$ sign and $T_{\text {? }}$ is som ew hat sm aller than $T_{k}$. A negative sign of the ratio of the two torque com ponents has


F IG . 7: D ependence of the spin-transfer torque $T_{k}$ and $T_{\text {? for }} \mathrm{C} \circ / \mathrm{Cu} / \mathrm{C} \circ(111)$ on the angle. The torques per surface atom are in units of $\mathrm{eV}_{\mathrm{b}}$. F igure (a) is for $\mathrm{M}=1$, and (b) for $\mathrm{M}=2 \mathrm{~m}$ onolayers of $\mathrm{C} O$ in the sw itch ing m agnet.
im portant and unexpected consequences for hysteresis loops as discussed in the next section. Finally, we show in $F$ ig. 8 the dependence of $T_{\text {? }}$ and $T_{k}$ on the thickness of the $C o$ sw itching $m$ agnet. It can be seen that


FIG. 8: D ependence of the spin-transfer torque $T_{k}$ and $T_{\text {? for }} \mathrm{Co} / \mathrm{Cu} / \mathrm{Co} \circ(111)$ on the thickness of the sw itch ing $m$ agnet $M$ for $==3$. The torques are in units of $e V_{b}$.
the out-of-plane torque $T_{\text {? }}$ becom es sm aller than $T_{k}$ for thicker sw itching $m$ agnets. $T$ his is the expected behavior since our polarizing $m$ agnet is sem i-in nite $C \circ$, so that as the sw itching $C \circ m$ agnet becom es thicker we approach the lim it of a sym m etric junction forwhich the $y$-com ponent of the spin current vanishes and the corresponding com ponent in the lead is usually sm all. H ow ever, $\mathrm{T}_{\text {? }}$ is by no m eans negligible (27\% of $\mathrm{T}_{\mathrm{k}}$ ) even for a typical experim ental thickness of the sw itching Co layer of ten atom ic planes. It is also interesting that beyond the $m$ onolayer thickness, the ratio of the tw o torques is positive $w$ th the exception of $M=4$.

STABILITY OF STEADY STATESAND HYSTERESIS LOOPS

In Sec. 4 we calculated the steady-state orientation of the $m$ agnetization of the sw itching $m$ agnet fully selfconsistently as a function ofbias $\mathrm{V}_{\mathrm{b}}$ (see F ig.3). These results allow us to calculate the continuous portions of the hysteresis loops of resistance versus bias, but to determ ine where jum ps occur wem ust investigate the stability of the steady states. T his cannot be done $w$ thin the standard $K$ eldysh form alism since the dynam ics of the system, inchuding dam ping, lies outside its scope. W e, therefore, $m$ ap the $m$ icroscopic problem onto a phenom enologicaltim e-dependent Landau- ifshitz (LL) equation with $G$ ilbert dam ping. An approach based
 we use as an input $m$ icroscopically determ ined torques $T_{k}, T_{\text {? }}$. In previous work only $T_{k}$ was considered and its m agnitude was an adjustable param eter. Secondly, the im portance of the steady state concept in the context of the LL equation has not previously been fully recognized. Finally, the consequences of easy plane anisotropy have hardly been explored; we nd that, in fact, it can lead to com pletely new sw itching scenarios when $T_{k}$ and $T_{\text {? }}$ have the opposite sign. Even in the absence of easy plane anisotropy, $T_{k}$ and $T_{\text {? }} w$ ith the opposite sign $m$ ay lead to qualitatively di erent types of sw itching.

In Sec. 6 the unit vector in the direction of the $s w$ itching $m$ agnet $m$ om ent $m$ was always taken in the $z$ direction but to discuss the LL equation wem ust consider $m$ in a generaldirection. The total spin-transfer torque $T \mathrm{~m}$ ay be written quite generally as the sum of the two com ponents in the directions of the vectors $m \quad p$ and $m$ ( $m \quad m$ ), where $p$ is a unit vector in the direction of the $m$ agnetization of the polarizing m agnet. Thus

$$
\begin{equation*}
\mathrm{T}=\mathrm{T}_{?}+\mathrm{T}_{\mathrm{k}} ; \tag{46}
\end{equation*}
$$

where

$$
\begin{gather*}
T_{?}=g_{?} \quad\left(\begin{array}{ll}
\mathrm{m} & \mathrm{p}) \\
\mathrm{T}_{\mathrm{k}}=g_{\mathrm{k}} \mathrm{~m} & (\mathrm{p} \\
\mathrm{m}
\end{array}\right): \tag{47}
\end{gather*}
$$

The m odulus of both vector products in Eqs.(47), (48) is equal to $\sin$, where (0) is the angle betw een $p$ and $m$. Since in the $S M T_{\text {? }}$ and $T_{k}$ depend only on the angle, it follows that the coe cients $g_{\text {? }}, g_{k}$ are functions only of. To determ ine $g_{\text {? }}(), g_{k}()$, we retum to the geom etry of Sec. 6 $w$ th $p=(\sin ; 0 ; \cos )$ and $m=(0 ; 0 ; 1)$. It follows that

$$
\begin{gather*}
\mathrm{T}_{\mathrm{k}}=g_{\mathrm{k}}()(\sin ; 0 ; 0)  \tag{49}\\
\mathrm{T}_{?}=g_{?}()(0 ; \sin ; 0): \tag{50}
\end{gather*}
$$

$T$ hus the scalar quantities calculated in Sec. 6 are $T_{k}=g_{k} \sin , T_{?}=g_{\text {? }} \sin . H$ ence the $m$ agnitudes and signs of $g_{k}(), g_{\text {? }}()$ are determ ined. It is seen in $F i g .4$ that the $\sin$ factor accounts for $m$ ost of the angular dependence of $T_{k}, T_{\text {? }}$ so that to a good approxim ation $g_{k}, ~ g_{\text {? }}$ are constants, proportional to bias.
$T$ he LL equation takes the form

$$
\begin{equation*}
\frac{d m}{d t}+m \quad \frac{d m}{d t}= \tag{51}
\end{equation*}
$$

w ith the reduced total torque given by

$$
\begin{equation*}
=\left(\mathrm{H}_{\mathrm{A}}<\mathrm{S}_{\text {tot }}>+\mathrm{T}_{?}+\mathrm{T}_{\mathrm{k}}\right)=\dot{k} \mathrm{~S}_{\text {tot }}>\dot{j} \tag{52}
\end{equation*}
$$

where $<S_{\text {tot }}>$ is the total_spin angular $m$ om entum of the sw itching $m$ agnet and is the $G$ ibert dam ping


$$
\begin{equation*}
\left(1+{ }^{2}\right) \frac{d m}{d t}=\quad \mathrm{m} \quad: \tag{53}
\end{equation*}
$$

We rst consider steady-state solutions of this equation but shall retum to the full tim e-dependent equation when discussing stability of these states. In the steady state $\mathrm{Eq}(51)$ reduces to

$$
\begin{equation*}
\mathrm{H}_{\mathrm{A}}<\mathrm{S}_{\mathrm{tot}}>+\mathrm{T}_{?}+\mathrm{T}_{\mathrm{k}}=0 \tag{54}
\end{equation*}
$$

which is equivalent to Eq.(33).
Them agnetization unit vectorp of the polarizing $m$ agnet is given by ( $\sin ; 0 ; 00 s$ ) and in the phenom eno-
 $m=(\sin \cos ; \sin \sin ; \cos )(\sec \mathrm{Fig} .1)$. The procedure for nding steady states is exactly analogous to
that described in Sec. 4 for the $m$ icroscopic approach. Thus the univensalpath on the unit sphere consisting of points ( ; ) which correspond to possible steady states, independent of bias, is again given by Eq.(34). For given the torque $T=T_{\text {? }}+T_{k}$ is now de ned explicitly as a function of and by Eqs. (47), (48), the bias factor in the constants $g_{\text {? }}, g_{k}$ cancelling as before. Sim ilarly, using Eq.(54), we can plot against bias $\mathrm{V}_{\mathrm{b}}$ for the actual steady state in the given bias as in F ig. 3 .

W e now retum to Eq.(51) to discuss stability of the steady states. The torque is given by

$$
\begin{equation*}
=H_{u 0} f\left(m x_{z}\right) m \quad e_{z} \quad h_{p}\left(m x_{Y}\right) m \quad e_{y}+v m \quad(p \quad m)+v r m \quad p g ; \tag{55}
\end{equation*}
$$

where the relative strength of the easy plane anisotropy $h_{p}=H_{p 0}=H_{u 0}$, using the notation of Eqs. (5), (6). $T$ he last two term $s$ correspond to $T_{k}$, $w$ th strength param eter $v$, and $T_{\text {? }}$, $w$ ith strength param eter rv. $C$ learly the reduced bias $v$ is proportional to the actualbias $V_{b}$ and inversely proportional to the num ber of atom ic planes in the sw itching $m$ agnet. C om paring Eqs.(47), (48), and (55) we see that $r=g_{\text {? }}=g_{k}$. Thus if the scalar torques $\mathrm{T}_{\mathrm{k}}, \mathrm{T}_{\text {? }}$ de ned afterEq. (50) have the sam e sign it follow $s$ that $r$ is positive. C onversely, $r$ is negative if the torques have opposite sign. W e now linearize Eq. (51) about a steady-state solution $m=m o r$, which satis es $=0$, using the local coordinate axes show in F ig.9. T hus


F IG.9: Local coordinate axes for the deviation of the $m$ agnetization $m$ from its steady-state orientation $m$.

$$
\begin{equation*}
m=m 0_{0}+e+e \tag{56}
\end{equation*}
$$

and the linearized Eq.(53) m ay be w ritten in the form

$$
\begin{equation*}
\frac{\mathrm{d}}{\mathrm{~d}}=\mathrm{A}+\mathrm{B} \quad ; \frac{\mathrm{d}}{\mathrm{~d}}=\mathrm{C}+\mathrm{D} ; \tag{57}
\end{equation*}
$$

where $A, B, C, D$ are functions of 0,0 , and the param eters $h_{p}, v, r$, and. Follow ing Sun [i-1], we have introduced the natural dim ensionless tim e variable $=t \mathrm{H}_{\mathrm{u} 0}=\left(1+{ }^{2}\right)$. The conditions for the steady state to be stable are

$$
\begin{equation*}
F=A+D \quad 0 ; G=A D \quad B C \quad 0 \tag{58}
\end{equation*}
$$

excluding $F=G=0\left[\overline{1}_{1}\right]$. The dam ping param eter appears in $G$ only as a factor $1+2$ and $m$ ay be cancelled in the condition for stability G 0 . This condition becom es

$$
\begin{align*}
& \left.h_{\mathrm{p}}^{2} \sin ^{2} \quad 0 \sin ^{2} \text { o( } 1 \quad 2 \sin ^{2} \quad 0 \sin ^{2} \quad 0\right) \quad 0 \text {; } \tag{59}
\end{align*}
$$

where $Q=p m m_{0}=\sin \sin 0 \cos 0+\cos \cos 0$. Sim ilarly, the condition $F \quad 0$ becom es

$$
2 \mathrm{v}(1+r) Q \quad\left(\cos 20+\cos ^{2} \quad 0\right) \quad h_{B}\left(\begin{array}{lllll}
1 & 3 \sin ^{2} & 0 & \sin ^{2} & 0 \tag{60}
\end{array}\right) \quad 0:
$$

A num ber of general conclusions can be drawn from these inequalities. How ever, we rst consider the special case when the $m$ agnetization of the polarizing $m$ agnet is in the direction of the uniaxial anisotropy axis of
the $s w i t c h i n g m$ agnet $(=0)$. In this case the equation $=0, w$ ith given by Eq. (55), show $s$ im $m$ ediately that possible steady states are given by $0=0$; corresponding to the sw itching layer $m$ om ent along the axis of the uniaxial anisotropy. These are the only solutions when $h_{p}=0$. H ow ever, in the presence of easy-plane anisotropy $\left(h_{p} \in 0\right)$ there are additional steady state directions of the sw itching layer $m$ om ent given by $\sin 20=2 v=h_{p}, \cos 0=\operatorname{vrcos} 0=(\cos 0+v \sin 0)$. In the pure Slonczew skicase of $T_{?}=0$ ( $r=0$ ) it follows that $0=2$. The stability conditions (59) and (60) then reduce to cos2 0 and $h_{p}\left(\begin{array}{lll}1 & 3 \sin ^{2} & 0\end{array}\right) \quad 1$ respectively. For practicalbiases $\mathrm{v}=\mathrm{h}_{\mathrm{p}} \quad 1$ and the solution for 0 satisfying the rst stability condition is $0=2 \mathrm{v}=\mathrm{q}$. The second stability condition is then not satis ed. Thus for $=0$, $r=0$ the only stable steady states of interest are given by $0=0$ or. It is easily seen that in this case the inequality (59) is alw ays satis ed and the system becom es unstable when the lefthand side of Eq.(60) changes sign at $v_{c}=\left(1+\frac{1}{2} h_{p}\right)$, corresponding to Sun's [']ld result in zero extemal eld. This show s clearly
 case is equivalent to the instability of a steady state in our approach.

In another special case when we have only out-of-plane torque $T_{\text {? }}$, the sw itching criteria are clearly the same as in the Stoner-W ohlfarth eld-sw itching theory since the torque $\mathrm{T}_{\text {? }}$ is equivalent to one arising from an e ective eld of $m$ agnitude $H_{10} \mathrm{Vr}$ (see Eq.(55)). The stability criteria are then equivalent to the conditions for a m inim um of an energy function whose gradient gives all the e ective elds. This was previously recognized by $H$ eide et al. [16]. O bviously this energy does not involve and the absence of in both criteria is clearly seen when in the second criterion (60) we take the lim it $v!0 ; r!1$ with the $T$ ? param eter vr nite. As soon as the in-plane torque param eter $v$ is nonzero, no energy function exists and the stability criterion (60) involves the dam ping param eter, show ing its essentially dynam ic nature. It is interesting that even when both spin-transfer torques exist, the in-plane torque drops out of Eq.(60) in the strong dam ping lim it ! 1 and we retum to a Stonerw ohlfarth situation.

In general, the system is neither in the Slonczew ski-Sun norStoner-W ohlfarth lim it and ourgeneralstability analysis based on the criteria (59) and (60) is required. W e shall rst apply it to discuss the stability of the steady-state paths shown in Fig. 3 which correspond to the $m$ icroscopic param eters (b) of Table I. In this case, the reduced param eters of the present section, which reproduce accurately the $m$ icroscopically determ ined curves in $F$ ig. 3, are $h_{p}=0$ and $r=1$. The torque ratio $r=1$ is clear from the curves for case (b) in Fig. 4. The corresponding steady-state paths are show $n$ in $F i g .10$ (a). In $F$ ig. 10 (b) we plot the steady-state paths for the param eter set (d) of Table $I$, in which case $r=1$ (see $F$ ig. 4). In $F$ ig. 3 we plotted $V_{b}$ on the bias axis, where $V_{b}$ is in volts, in order to com pare $w$ th the present reduced bias $v$ which is proportional to $\mathrm{eV}_{\mathrm{b}}$ and e is negative. $\left(\mathrm{V}_{\mathrm{b}}\right.$ and v have the sam e sign w hen $\mathrm{T}_{\mathrm{k}}<0$ and opposite sign when $\mathrm{T}_{\mathrm{k}}>0$.) W e have chosen for presentation punposes a value $=0: 05$ of the dam ping param eter which is


FIG. 10: R educed bias v required to stabilize the sw itching $m$ agnet $m$ om ent at an angle on the universalpath for $r=1$ (a) and $r=1$ (b) and $h_{p}=0$. B old lines correspond to stable steady states.
som ew hat larger than that suggested in the m om ent of the polarizing m agnet is at $=2$ radians. We rst discuss Fig .10 (a). Initially with zero bias $v$ the $m$ om ent of the $s w$ itching $m$ agnet is in the direction of the uniaxial anisotropy eld, i.e., $0=0$. A s v increases positively, o increases until the stability criterion (60) ceases to be satis ed. In Fig. 10 stable
steady states are indicated by heavy lines and unstable ones by thin lines. At this value of $v$, the point A in Fig. 10 (a), the system seeks another steady state which is stable at the sam e bias and hence jum ps to B. It is assum ed that for nite the system will home in on the stable state. Sun [1] [] showed how this happens dynam ically for the special case of $=0$. On further increase of bias the system proceeds to $C$ and, on reducing the bias to zero, it m oves to $D$ where $=$. The current-induced sw itching process is thus com pleted with the $m$ agnetization sw itched betw een the two stable zero-bias orientations ( $=0$ and ) in the uniaxial anisotropy eld. To reverse the process the bias is reversed and the system proceeds to E where it becom es unstable and jumps to F.F inally a further negative increase of $v$ takes the system to $G$ and, on reducing the bias to zero, we retum to $O$. If the resistance is calculated for each steady state, using our $K$ eldysh form alism (or equivalently the $K$ ubo form ula) for charge current, the corresponding hysteresis loop of resistance versus bias can be plotted. W e shall do this for later exam ples.

In the above exam ple, the in-plane and out-of-plane torques are of equal strength and of the sam e sign ( $r=1$ ). The instabilities at A and E are govemed by the dynam icalcriterion (60). In the Stoner-W ohlfarthlike case discussed earlier the system rem ains stable, as bias is increased, up to the maxim um at A'. The rst criterion (59) determ ines the instability at this point and sim ilarly at E'.
$F$ ig. 10b show s the situation for the less usual case of negative $r$, in particular $r=1$ corresponding to param eter set ( d ). Starting at $0=0, w$ th bias increasing from zero, an instability occurs at A as before. H ow ever, there are now two possible stable steady states to which the system $m$ ight jum $p$, labelled by $B^{\prime}$ and B.W e cannot say to which point the jum p occurs w ithout follow ing the detailed dynam ics of the system $w$ ith tim e-dependent solutions of the Landau-Lifshitz equation. If the system jumps to $B^{\prime}$ further increase of bias leads tow ards $G$ where the $m$ om ent of the $s w$ itching $m$ agnet approaches alignm ent $w$ ith that of the polarizing $m$ agnet. H ow ever the bias is varied now, through positive and negative values, the system rem ains on the stable steady state branch G G' and no sw itching to the point D can occur. If, how ever, the system jum ps from A to B, the bias can be reduced to zero at D and a hysteresis loop can be com pleted via E and F.On the other hand if on jum ping to $B$ the bias is further increased, to reach the state $C$, a jum $p$ willoccur to $C^{\prime}$ and the system is again trapped on the branch G G'.
$T$ he next exam ple we consider em ploys a $m$ apping of the fully realistic $m$ icroscopic torques for C o/Cu(111) show $n$ in $F$ ig. 7b onto the $m$ acroscopic $m$ odel. In this case the $s w i t c h i n g m$ agnet consists of $t w o$ atom ic planes of cobalt ( $M=2$ ). We recall that the nonm agnetic spacer consists of 20 atom ic planes of $C u$. A new feature of this exam ple is that we now introduce a strong easy-plane anisotropy $w$ ith $h_{p}=100$. If we take $H_{u 0}=1: 86 \quad 10^{\circ} \sec ^{1}$ corresponding to an uniaxial anisotropy eld of about 0.01 T , this value of $h_{p}$

 value of $r$ which gives a reasonable $t$ to the $m$ icroscopic torques shown in $F$ ig. 7 b is $r=0: 65$. We nd that the strong easy-plane anisotropy forces the switching $m$ agnet $m$ om ent to rotate in the ( $x$; $z$ ) plane, which m eans that the universal paths in the ( ; ) plane are alm ost straight lines with $=0$ or . The plot of reduced bias v against is show n in Fig. 11 and again the heavy portions of the curves indicate stable steady states. The multiple loops of steady states in $F$ ig. 11a are a new feature appearing for $h_{p} \in 0$. H ow ever, in this case, they are all unstable. T he im portant parts of the curves are shown on a larger scale in Fig.11b. This clearly resem bles Fig. 10a and instabilities now occur at the extrem alpoints A' and E' instead of A and $E$ as in $F$ ig.10a. In general, the point $A$ lies further up the curve tow ards $A$ ' the larger the product $h_{p}$. $T$ his follow s from Eq.(60) as long as the easy-plane anisotropy is strong enough for jsin $0 \sin 0 \dot{k} 1=\overline{3}$ to be satis ed. This stabilizing e ect of easy-plane anisotropy has the unw elcom e consequence that the critical bias (current) for sw itching is strongly increased by such anisotropy. The corresponding hysteresis loop of resistance versus bias for $=2$ radians is show $n$ in Fig . 12 a . W e have also transferred the key points from Fig. 11b. In Fig. 12b we show the hysteresis loop for $=3$ radians, which is close to $=$ assum ed in

$=2$ and $=3$ radians. $W$ hen this bias is converted to the current density using the calculated ballistic resistance of the junction, we nd that the critical current for switching is $10 \mathrm{~A}=\mathrm{cm}^{2}$, which is in very good agreem ent w ith experim ent [3]ld. H ow ever, there is a qualitative di erence between the cases $=2$ and $=3$ radians. For $=2$ radians, sw itching is detem ined by the instability condition (59) which is independent of the dam ping param eter. This means that switching is of the Stoner $-\mathbb{W}$ ohlfarth type. On the other hand, for $=3$ radians, we nd that the instability is determ ined by Eq. (60), which m eans that


F IG. 11: Reduced bias v required to stabilize the $\mathrm{C} \circ \mathrm{sw}$ itching magnet m om ent at an angle, w ith $=2$, and realistic an isotropy and dam ping param eters for $\mathrm{Co} / \mathrm{Cu} / \mathrm{Co(111)} \mathrm{w}$ ith $\mathrm{M}=2$. The value 0 is obtained for $v>0$ and $\quad$ is obtained for $\mathrm{v}<0$.


F IG . 12: R esistance of the $\mathrm{C} \circ / \mathrm{Cu} / \mathrm{C} \circ$ (111) junction as function of applied bias $w$ ith $\mathrm{M}=2 \mathrm{~m}$ onolayers of $\mathrm{C} \circ$ in the sw itch ing m agnet. (a) is for $=2$ radians and (b) is for $=3$ radians.

Sw itching is of the Slonczew ski-Sun type.
The last exam ple we consider em ploys again a mapping of the fully realistic $m$ icroscopic torques for $\mathrm{Co} / \mathrm{Cu}(111)$ show n in F ig. 7a onto the m acroscopic m odel. In this case the num ber of atom ic planes in the sw itching $m$ agnet is $M=1$. W e use the sam e values of $h_{p}, \quad, H_{u 0}$, and as in the previous exam ple. The best $t$ to the $m$ icroscopic torques in $F$ ig. 7a gives $r=1: 0$. This exam ple, besides being again a realistic one, introduces the feature of negative $r$ which we $m$ et in the single-orbitalm odel with param eter set (d) (see Figs. 4 and 10b). The plot of reduced bias $v$ against is show $n$ in $F$ ig. 13 w ith stable steady states indicated as before. T he low tbias part of the curves is plotted in $F$ ig. 13b on a larger scale. The fact that $j r j$ is com parable for $F$ igs. 11 and 13 (of the order of 1) but the sign is changed, leads to all the bias curves being essentially only re ected in the axis. H ow ever, the change of sign of $r$ is seen to have a dram atic e ect on the stability of the steady states. The most striking e ect is the creation of a 'bias-gap' with no stable steady states for values of reduced bias jv jbetw een about 0.7 and 10 . For $r=1$ the bias-gap only exists in the presence of easy-plane anisotropy. In this connection we m ay com pare F ig. 13 , w ith param eters $r=1, h_{p}=100,=0: 01,=2 \mathrm{w}$ th F ig. 10 b correponding to $\mathrm{r}=1, \mathrm{~b}=0,=0: 05,=2$. (The larger value of for Fig.10b is not im portant; it was used to push the point of instability $A$ to larger bias and thus clarify the gure). C learly there is no bias-gap in $F$ ig. 10 b w ith $h_{p}=0$. A nother e ect of large $h_{p}$ is to push the point of instability $G$ in $F$ ig. 13b to $m$ uch largerbias than the corresponding point in $F$ ig.10b, even $w$ th a sm aller dam ping param eter. In fact, for the particular values of and $h_{p}$ used for $F$ ig. 13, $G$ lies at a larger bias than $\mathrm{E}^{\prime}$. T he resultant hysteresis loop, shown in F ig.14a, is thus executed in the sam e


F IG. 13: Reduced bias v required to stabilize the $\mathrm{C} \circ \mathrm{sw}$ itching magnet m om ent at an angle, w ith $=2$, and realistic an isotropy and dam ping param eters for $\mathrm{Co} / \mathrm{Cu} / \mathrm{Co(111)} \mathrm{w}$ ith $\mathrm{M}=1$. The value 0 is obtained for $v<0$ and is obtained for $v>0$.
sense as that shown in Fig.12a. H ow ever in Fig. 14b, corresponding to $=3$ instead of 2 , the sense is reversed. In $F$ ig. 12 as we change bias from $B$ to $C$ or from $F$ to $G$ we are achieving saturation by aligning


F IG. 14: Resistance of the $\mathrm{Co} / \mathrm{Cu} / \mathrm{Co(111)}$ junction as a function of applied current, with $\mathrm{M}=1 \mathrm{~m}$ onolayer of $\mathrm{C} \circ$ in the SW itching $m$ agnet. (a) is for $=2$ radians and (b) is for $=3$ radians.
the sw itching $m$ agnet parallel or antiparallel to the polarizing $m$ agnet. H ow ever, in $F$ ig. 14 as we increase bias from $F$ the steady state becom es unstable at the point $G$, for a criticalbias, but there is no stable state for the system to jum $p$ to $w$ ith further increase ofbias (see Fig. 13b). To em phasize this point, the points G and $C$ are starred in $F$ ig. 14a. Thus for bias larger than this critical one the system cannot hom e in on any stable state and the $m$ om ent of the $s w i t c h i n g m$ agnet rem ains perpetually in a tim e-dependent state. For $m$ uch larger bias the system can hom $e$ in onto the stable $m$ ultiple loop states show in $F$ ig. 13a. T hus there is a range ofbias where only the tim e-dependent state is possible. T he bottom of the gap occurs at the bias point $G$ in $F$ ig. 14a. If the bias is then reduced below this value the system $w$ ill hom e in on a stable steady state and the hysteresis loop can be com pleted.

W e investigated the critical negative value of $r$ at which the bias gap appears. For the param eters used above, the gap is not present for $r=0: 05$ but is already wellestablished for $r=0: 1$. T hus when in $\mathrm{p}=\mathrm{plane}$ and out-ofplane spin-transfer torques have opposite sign, and easy plane an isotropy is large, only a sm allout-of-plane torque is required to produce this unusualbias gap behavior. Since out-of-plane torque corresponds to an e ective eld, we believe that this behavior is closely related to the tim e-dependent motion of the m om ent of the $s w$ itching $m$ agnet which is observed in a su ciently large applied $m$ agnetic eld '[b]. This
altemative $m$ echanism for tim e-dependent $m$ otion of the $s w$ itching $m$ agnet $m$ om ent is under investigation.
Even in the absence of easy plane anisotropy, but with large negative $r$, we have found a critical bias above which only tim e-dependent solutions exist. H ow ever, for sm all negative r (jr j 1) norm al solutions can occur (no bias gap). For interm ediate values of $r$, as discussed for $r=1 \mathrm{w}$ th reference to $F$ ig. 10 b , switching $m$ ay or $m$ ay not occur. Furtherm ore, in the case of pure in-plane torque ( $r=0$ ) and no easy plane anisotropy we nd straightforw ard switching of Slonczew ski-Sun type for jcos $\gg 1=3$, while for jcos je $1=3$ a m ore com plicated hysteresis loop is found.

CONCLUSIONS

O ur principal result is that spin-transfer torques responsible for current-induced sw itching of m agnetization can be calculated quantitatively for real system such as $\mathrm{Co} / \mathrm{Cu} / \mathrm{Co}$ junction in the ballistic regime using nonequilibrium $K$ eldysh form alism. In fact, we argue that the spin-transfer torque can be calculated selfconsistently from rst principles only in a steady state (sw itching $m$ agnet $m$ agnetization does not $m$ ove), and this is precisely what the $K$ eldysh form alism is designed for. In the sm allbias (linear-response) regim e higher-order ( $m$ any-body) e ects can be neglected and our results for the spin-transfer torque are, therefore, quite rigorous. $K$ eldysh form alism provides an explicit form ula for the local spin current betw een any two atom ic planes of the junction in term $s$ of one-electron surface $G$ reen functions for the cut junction. $T$ he surface $G$ reen functions are readily available and we calculate them using a tight-binding $H$ am iltonian $w$ ith param eters determ ined from $a t$ to an $a b$ initio band structure. $W$ ith the exception of Slonczew ski's parabolic band calculation [llill, our K eldysh form ulation is the only theory that yields the local spin current taking into into account rigorously contributions from all the parts of the junction. As the follow ing ar-
 incident from the spacer on the spacer/sw itching m agnet interface are incom plete. W hen the particle current
ow from the polarizing $m$ agnet tow ard the switching $m$ agnet it is clear that a spin-transfer torque acts on the sw itching $m$ agnet. H ow ever, when the polarity of the applied bias is reversed, the current incident from the right lead on the $s w i t c h i n g m$ agnet is unpolarized and, therefore, has no e ect on it. On the other hand, it is well know $n$ experim entally [3] $[3]$ that changing the polarity of the bias reverses the direction of the spin-transfer torque (the $m$ agnitude rem ains the sam e). This cannot be explained $w$ ithin a theory that treats only the spacer/sw itching $m$ agnet interface. The ingredient that is $m$ issing is strong re ection of electrons from the polarizing $m$ agnet which results in a spin polarization of the re ected electrons. $C$ learly only such re ected spin current ow ing in the direction opposite to that of the particle current can exert torque on the switching $m$ agnet. It follows that $m$ ultiple re ections of electrons from the polarizing and sw itching $m$ agnet are an essential feature of the problem. They are treated rigorously to all orders in our theory. The fiundam ental experim ental fact that the spin-transfer torque acting on the sw itching $m$ agnet is proportional to the applied bias is obtained naturally in our theory since the spin current anyw here in the junction, given by Eq. (25), is proportional to the di erence betw een the Ferm i functions for the left and right halves of the cut junction, i.e., proportional to the bias in the low toias (linear-response) lim it. These argum ents indicate that selfconsistent treatm ent of the whole junction is crucial for correct understanding of current-induced sw itching ofm agnetization.

The spin-transfer torque calculated from our $K$ eldysh form alism has tw o com ponents, one w the torque vector $\mathrm{T}_{\mathrm{k}}$ in the plane containing the m agnetizations of the two m agnetic layers ('in-plane' torque) and anotherw ith the torque vector $T_{\text {? }}$ perpendicular to this plane ('out-ofplane' torque). It is generally believed that the e ective eld-like component $T$ is always $s m$ all. $W e$ nd that this is not the case and our calculations show that, in general, both the in-plane and out-of-plane com ponents tend to nite values independent of the spacer thickness in the lim it of a thick spacer. However, it is true that $T_{\text {? }}$ is strictly zero in the lim it of an in nite exchange splitting betw een the majority and m inority-spin bands in both ferrom agnets, and this is the case considered intially by Slonczew ski M1]. In the realistic case of a nite exchange splltting, $T_{\text {? }}$ is nonzero and can be com parable with $T_{k}$. The only other general case when $T_{\text {? }}$ can be small occurs for a junction $w$ ith re ection symm etry about a plane at the center of the spacer. $H$ ence to observe an $e$ ect of $T_{\text {? }}$ one needs to break the re ection sym m etry of the junction. For a junction $w$ ith polarizing and sw itching $m$ agnets $m$ ade of the sam e $m$ aterial, this is achieved by $m$ aking the sw itching $m$ agnet thinner than the polarizing $m$ agnet, and a strongest e ect is found for a sw itching $m$ agnet only a few
atom ic planes thick. O ur calculations show that $T_{\text {? }}$ and $T_{k}$ are comparable for a $\mathrm{Co} / \mathrm{Cu} / \mathrm{Co}$ (111) junction when the sw itching C o layer is one or tw o atom ic planes thick. N evertheless, for a good epitaxial junction (ballistic lim it), we nd that $T_{?}$ is $27 \%$ of $T_{k}$ even for a sw itching $C \circ m$ agnet as thick as ten atom ic planes. An altemative way to break the sym $m$ etry is to use a junction $w$ ith polarizing and sw itching $m$ agnets $m$ ade of di erent materials.

A nother result wew ish to highlight is that, depending on $m$ aterial param eters of the junction, the relative sign of $T_{\text {? }}$ and $T_{k}$ can be negative as well as positive. For exam ple, $T_{?}=T_{k}<0$ for Co/Cu/Co(111) w th a sw itching $\mathrm{C} \circ \mathrm{m}$ agnet of one atom ic plane and $\mathrm{T}_{\text {? }}=\mathrm{T}_{\mathrm{k}}>0$ for two atom ic planes of $\mathrm{C} \circ$. The negative sign of the ratio $T_{?}=T_{k}$ has a profound $e$ ect on the stability of steady states and, hence, on the nature of current-induced sw itching.
$F$ inally, to determ ine the critical currents for sw itching and to investigate the ect of $T_{\text {? }}$, we have used the $m$ icroscopically calculated spin-transfer torques as an input into the phenom enological Landau-七ifshitz equation with G ibert dam ping. O ur general philosophy is that all steady states can be calculated from
rst principles and loss of their stability, determ ined from the Landau-Lifshitz equation, corresponds to sw itching. T his holds provided there is another stable steady state at the sam e current density the system can sw itch into. W e show ed that our criterion for instability of the steady state leads to the sam e critical

betw een the polarizing and sw itching $m$ agnet $m$ om ents equalto 0 or. H ow ever, we nd that qualitatively di erent sw itching scenarios can occur when $T_{?}=T_{k} \not 0,0$, and in the presence of an easy-plane (shape) anisotropy. In particular, when the easy-plane anisotropy is strong, even a relatively sm all $T_{\text {? }}$ ( $5-10 \%$ of $\mathrm{T}_{\mathrm{k}}$ ) has a strong e ect on switching. In the absence of an applied magnetic eld, we nd that an ordinary hysteresis loop is the only possible sw itching scenario when $T_{?}=T_{k}>0$. H ow ever, for $T_{?}=T_{k}<0$, a norm al hysterestic sw itching occurs only at relatively low current densities. W hen the current exceeds a critical value, there are no stable steady states and the system thus rem ains perm anently in a tim e dependent state. $T$ his is analogous to the observed precession of the sw itching $m$ agnet $m$ agnetization caused by a D C current
 this behavior, is proportional to the D C current and, hence, com plete loss of stability of the steady state occurs only when this term is large enough, i.e., when the D C current is above a critical value.

O ur calculations for $\mathrm{C} \circ / \mathrm{Cu} / \mathrm{C} \circ(111)$ show that the critical current for switching in the hysteretic regim e is $10 \mathrm{~A}=\mathrm{cm}^{2}$ both for $\mathrm{C} \circ \mathrm{sw}$ itching m agnets of one and two atom ic planes. This is in good agreem ent w ith experim ent [3] a fully realistic $\mathrm{Co} / \mathrm{Cu} / \mathrm{C} \circ$ (111) junction and assum ing a uniaxial anisotropy of $0: 01 \mathrm{~T}$ and G ibert dam ping $=0: 01$. This is in line w the values of the uniaxial anisotropy and $G$ ilbert dam ping quoted by Sun [思].
W e conclude by stressing that all the speci c results we have obtained are strictly valid for a perfect epitaxial junction, i.e., in the ballistic lim it. H ow ever, the K eldysh form alism we have described is valid also in the di usive lim it. Generalization to the di usive lim it is, in principle, straightforw ard. For exam ple, one could introduce random im purities in the lateral supercell geom etry, determ ine the one-electron surface G reen functions in this geom etry and then perform con guration averaging of the spin current.

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